

Title (en)
NON-VOLATILE STORAGE CELL

Title (de)
NICHTFLÜCHTIGE SPEICHERZELLE

Title (fr)
CELLULE MEMOIRE NON VOLATILE

Publication
EP 0916161 A1 19990519 (DE)

Application
EP 97937411 A 19970729

Priority
• DE 9701600 W 19970729
• DE 19631147 A 19960801

Abstract (en)
[origin: WO9806139A1] The invention concerns a non-volatile write-once storage cell comprising a MOS transistor which, as gate dielectric, has a triple dielectric layer consisting of a first silicon oxide layer (51), a silicon nitride layer (52) and a second silicon oxide layer (53). The first silicon oxide layer (51) and the second silicon oxide layer (53) are each at least 3 nm thick. The storage cell is not erasable and can hold data for a period of more than 1000 years.

IPC 1-7
H01L 29/792

IPC 8 full level
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